

# DS15BR400, DS15BR401

SNLS224F-AUGUST 2006-REVISED DECEMBER 2010

# DS15BR400/DS15BR401 4-Channel LVDS Buffer/Repeater with Pre-Emphasis

Check for Samples: DS15BR400, DS15BR401

# FEATURES

- DC to 2 Gbps Low Jitter, High Noise Immunity, Low Power Operation
- 6 dB of Pre-emphasis Drives Lossy Backplanes and Cables
- LVDS/CML/LVPECL Compatible Input, LVDS Output
- On-chip 100 Ω output termination, optional 100 Ω Input Termination
- 15 kV ESD Protection on LVDS Inputs and

### Outputs

- Single 3.3V Supply
- Industrial -40 to +85°C Temperature Range
- Space Saving WQFN-32 or TQFP-48 Packages

## **APPLICATIONS**

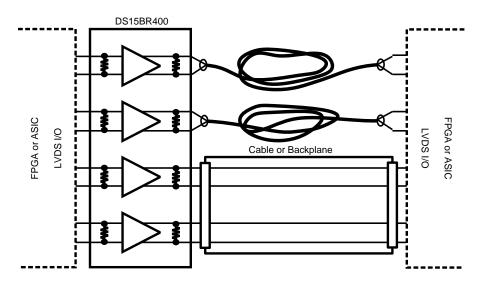
- Cable Extension Applications
- Signal Repeating and Buffering
- Digital Routers

## DESCRIPTION

The DS15BR400/DS15BR401 are four channel LVDS buffer/repeaters capable of data rates of up to 2 Gbps. High speed data paths and flow-through pinout minimize internal device jitter and simplify board layout, while pre-emphasis overcomes ISI jitter effects from lossy backplanes and cables. The differential inputs interface to LVDS, and Bus LVDS signals such as those on National's 10-, 16-, and 18- bit Bus LVDS SerDes, as well as CML and LVPECL. The differential inputs and outputs of the DS15BR400 are internally terminated with 100 $\Omega$  resistors to improve performance and minimize board space. The DS15BR401 does not have input termination resistors. The repeater function is especially useful for boosting signals for longer distance transmission over lossy cables and backplanes.

The DS15BR400/DS15BR401 are powered from a single 3.3V supply and consume 578 mW (typ). They operate over the full -40°C to +85°C industrial temperature range and are available in space saving WQFN-32 and TQFP-48 packages.

## **Typical Application**



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#### **Block and Connection Diagrams**

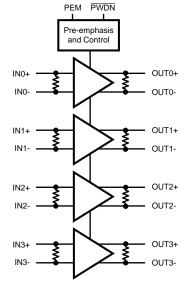
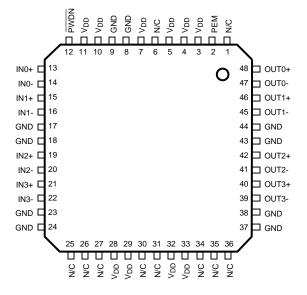


Figure 1. DS15BR400 Block Diagram





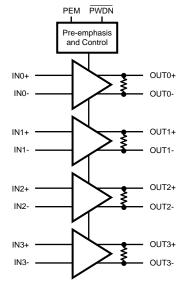
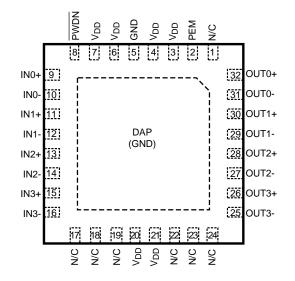


Figure 2. DS15BR401 Block Diagram



#### Figure 4. WQFN Pinout - Top View Package Number RTV0032A

Pin Name	TQFP Pin Number	WQFN Pin Number	I/O, Type	Description
DIFFERE	NTIAL INPUTS			
IN0+ IN0-	13 14	9 10	I, LVDS	Channel 0 inverting and non-inverting differential inputs.
IN1+ IN1-	15 16	11 12	I, LVDS	Channel 1 inverting and non-inverting differential inputs.
IN2+ IN2-	19 20	13 14	I, LVDS	Channel 2 inverting and non-inverting differential inputs.
IN3+ IN3-	21 22	15 16	I, LVDS	Channel 3 inverting and non-inverting differential inputs.

#### **PIN DESCRIPTIONS**

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#### **PIN DESCRIPTIONS (continued)**

Pin Name	TQFP Pin Number	WQFN Pin Number	I/O, Type	Description
DIFFERE	ENTIAL OUTPUTS	, ,		
OUT0+ OUT0-	48 47	32 31	O, LVDS	Channel 0 inverting and non-inverting differential outputs. <sup>(1)</sup>
OUT1+ OUT1-	46 45	30 29	O, LVDS	Channel 1 inverting and non-inverting differential outputs. (1)
OUT2+ OUT2-	42 41	28 27	O, LVDS	Channel 2 inverting and non-inverting differential outputs. (1)
OUT3+ OUT3-	40 39	26 25	O, LVDS	Channel 3 inverting and non-inverting differential outputs. (1)
DIGITAL	CONTROL INTER	RFACE		
PWDN	12	8	I, LVTTL	A logic low at PWDN activates the hardware power down mode (all channels).
PEM	2	2	I, LVTTL	Pre-emphasis Control Input (affects all Channels)
POWER		•		•
V <sub>DD</sub>	3, 4, 5, 7, 10, 11, 28, 29, 32, 33	3, 4, 6, 7, 20, 21	I, Power	$V_{DD} = 3.3V, \pm 10\%$
GND	8, 9, 17, 18, 23, 24, 37, 38, 43, 44	5 (2)	I, Ground	Ground reference for LVDS and CMOS circuitry. For the WQFN package, the DAP is used as the primary GND connection to the device in addition to the pin numbers listed. The DAP is the exposed metal contact at the bottom of the WQFN-32 package. It should be connected to the ground plane with at least 4 vias for optimal AC and thermal performance.
N/C	1,6, 25, 26, 27, 30, 31, 34, 35, 36	1, 17, 18,19,22, 23, 24		No Connect

(1) The LVDS outputs do not support a multidrop (BLVDS) environment. The LVDS output characteristics of the DS15BR400 and DS15BR401 are optimized for point-to-point backplane and cable applications.

(2) Note that for the WQFN package the GND is connected thru the DAP on the back side of the WQFN package in addition to the actual pin numbers listed.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



## Absolute Maximum Ratings<sup>(1)</sup>

CMOS Input Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Receiver Input Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Driver Output Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Output Short Circuit Current         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Output Short Circuit Current         +40 mA           Junction Temperature         -65°C to +150°C           Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         260°C           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         33.3mW/°C           ESD Last Passing Voltage         8 kV		
LVDS Receiver Input Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Driver Output Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Output Short Circuit Current         +40 mA           Junction Temperature         +150°C           Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         1.64W           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         33.3mW/°C           ESD Last Passing Voltage         8 kV           LVDS pins to GND only         5 kV           EIAJ, 0Q, 200PF         250V	Supply Voltage (V <sub>DD</sub> )	-0.3V to +4.0V
LVDS Driver Output Voltage         -0.3V to (V <sub>DD</sub> +0.3V)           LVDS Output Short Circuit Current         +40 mA           Junction Temperature         +150°C           Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         1.64W           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         13.2mW/°C           WQFN         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           HBM, 1.5kQ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Q, 200pF         250V	CMOS Input Voltage	-0.3V to (V <sub>DD</sub> +0.3V)
LVDS Output Short Circuit Current         +40 mA           Junction Temperature         +150°C           Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         260°C           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         33.3mW/°C           ESD Last Passing Voltage         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	LVDS Receiver Input Voltage	-0.3V to (V <sub>DD</sub> +0.3V)
Junction         +150°C           Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         260°C           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         76°C/W           WQFN         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         33.3mW/°C           ESD Last Passing Voltage         8 kV           LVDS pins to GND only         8 kV           EIAJ, 0Ω, 200pF         250V	LVDS Driver Output Voltage	-0.3V to (V <sub>DD</sub> +0.3V)
Storage Temperature         -65°C to +150°C           Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         1.64W           TQFP         1.64W           WQFN         7.6°C/W           TQFP         76°C/W           WQFN         76°C/W           Package Derating above +25°C         76°C/W           TQFP         13.2mW/°C           YWFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           LVDS pins to GND only         8 kV           EIAJ, 0Ω, 200pF         250V	LVDS Output Short Circuit Current	+40 mA
Lead Temperature (Solder, 4sec)         260°C           Max Pkg Power Capacity @ 25°C         1.64W           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         76°C/W           WQFN         76°C/W           Package Derating above +25°C         73.2mW/°C           TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	Junction Temperature	+150°C
Max Pkg Power Capacity @ 25°C         1.64W           TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         76°C/W           WQFN         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           HBM, 1.5kΩ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	Storage Temperature	-65°C to +150°C
TQFP         1.64W           WQFN         4.16W           Thermal Resistance (θ <sub>JA</sub> )         76°C/W           TQFP         76°C/W           WQFN         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           HBM, 1.5kΩ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	Lead Temperature (Solder, 4sec)	260°C
TQFP         76°C/W           WQFN         30°C/W           Package Derating above +25°C         13.2mW/°C           TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           HBM, 1.5kΩ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V		
TQFP         13.2mW/°C           WQFN         33.3mW/°C           ESD Last Passing Voltage         8 kV           HBM, 1.5kΩ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	TQFP	
HBM, 1.5kΩ, 100pF         8 kV           LVDS pins to GND only         15 kV           EIAJ, 0Ω, 200pF         250V	TQFP	
EIAJ, 0Ω, 200pF 250V		8 kV
	LVDS pins to GND only	15 kV
Charged Device Model 1000V	EIAJ, 0Ω, 200pF	250V
	Charged Device Model	1000V

(1) Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of products outside of recommended operation conditions.

#### **Recommended Operating Conditions**

Supply Voltage (V <sub>DD</sub> )	3.0V to 3.6V
Input Voltage (V <sub>I</sub> ) <sup>(1)</sup>	0V to V <sub>DD</sub>
Output Voltage (V <sub>O</sub> )	0V to V <sub>DD</sub>
Operating Temperature (T <sub>A</sub> )	
Industrial	-40°C to +85°C

(1) V<sub>ID</sub> max < 2.4V

## **Electrical Characteristics**

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	<b>Тур</b> (1)	Max	Units
LVCMOS	DC SPECIFICATIONS (PWDN,	PEM)				•
V <sub>IH</sub>	High Level Input Voltage		2.0		V <sub>DD</sub>	V
V <sub>IL</sub>	Low Level Input Voltage		GND		0.8	V
I <sub>IH</sub>	High Level Input Current	$V_{IN} = V_{DD} = 3.6V (\overline{PWDN} \text{ pin})$	-10		+10	μA
I <sub>IHR</sub>	High Level Input Current	$V_{IN} = V_{DD} = 3.6V$ (PEM pin)	40		200	μA
IIL	Low Level Input Current	$V_{IN} = V_{SS}, V_{DD} = 3.6V$	-10		+10	μA
C <sub>IN1</sub>	LVCMOS Input Capacitance	Any Digital Input Pin to $V_{\mbox{\scriptsize SS}}$		5.5		pF
V <sub>CL</sub>	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}, V_{DD} = 0 \text{V}$	-1.5	-0.8		V

(1) Typical parameters are measured at  $V_{DD}$  = 3.3V,  $T_A$  = 25°C. They are for reference purposes, and are not production-tested.



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# **Electrical Characteristics (continued)**

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	<b>Тур</b> (1)	Max	Units
LVDS IN	PUT DC SPECIFICATIONS (INn	±)			·	
V <sub>TH</sub>	Differential Input High Threshold <sup>(2)</sup>	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$		0	100	mV
V <sub>TL</sub>	Differential Input Low Threshold <sup>(2)</sup>	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$	-100	0		mV
V <sub>ID</sub>	Differential Input Voltage	$V_{CM} = 0.8V$ to 3.55V, $V_{DD} = 3.6V$	100		2400	mV
V <sub>CMR</sub>	Common Mode Voltage Range	$V_{ID} = 150 \text{ mV}, V_{DD} = 3.6 \text{V}$	0.05		3.55	V
C <sub>IN2</sub>	LVDS Input Capacitance	IN+ or IN- to V <sub>SS</sub>		3.0		pF
I <sub>IN</sub>	Input Current	V <sub>IN</sub> = 3.6V, V <sub>DD</sub> = 3.6V	-10		+10	μA
		$V_{IN} = 0V, V_{DD} = 3.6V$	-10		+10	μA
LVDS O	UTPUT DC SPECIFICATIONS (C	DUTn±)				
V <sub>OD</sub>	Differential Output Voltage, 0% Pre-emphasis <sup>(2)</sup>	$R_L = 100\Omega$ external resistor between OUT+ and OUT- Figure 5	250	360	500	mV
$\Delta V_{OD}$	Change in V <sub>OD</sub> between Complementary States		-35		35	mV
V <sub>OS</sub>	Offset Voltage (3)		1.05	1.18	1.475	V
ΔV <sub>OS</sub>	Change in V <sub>OS</sub> between Complementary States		-35		35	mV
C <sub>OUT</sub>	LVDS Output Capacitance	OUT+ or OUT- to V <sub>SS</sub>		2.5		pF
I <sub>OS</sub>	Output Short Circuit Current	OUT+ or OUT- Short to GND		-21	-40	mA
		OUT+ or OUT- Short to VDD		6	40	mA
SUPPLY	CURRENT (Static)		·			
I <sub>CC</sub>	Supply Current	All inputs and outputs enabled and active, terminated with differential load of $100\Omega$ between OUT+ and OUT PEM = L		175	215	mA
I <sub>CCZ</sub>	Supply Current - Power Down Mode	$\overline{PWDN} = L, PEM = L$		20	200	μA
SWITCH	ING CHARACTERISTICS-LVD	S OUTPUTS				
t <sub>LHT</sub>	Differential Low to High Transition Time <sup>(4)</sup>	Use an alternating 1 and 0 pattern at 200 Mbps, measure between 20% and 80% of $V_{OD}$ .		170	250	ps
t <sub>HLT</sub>	Differential High to Low Transition Time <sup>(4)</sup>	Figure 6, Figure 8		170	250	ps
t <sub>PLHD</sub>	Differential Low to High Propagation Delay	Use an alternating 1 and 0 pattern at 200 Mbps, measure at 50% $V_{\text{OD}}$ between input to output.		1.0	2.0	ns
t <sub>PHLD</sub>	Differential High to Low Propagation Delay	Figure 6 , Figure 7		1.0	2.0	ns
t <sub>SKD1</sub>	Pulse Skew (4)			10	60	ps
t <sub>SKCC</sub>	Output Channel to Channel Skew <sup>(4)</sup>	Difference in propagation delay (t <sub>PLHD</sub> or t <sub>PHLD</sub> ) among all output channels.		25	75	ps
t <sub>SKP</sub>	Part to Part Skew <sup>(4)</sup>	Common edge, parts at same temp and V <sub>CC</sub>			550	ps

- Differential output voltage  $V_{OD}$  is defined as ABS(OUT+-OUT-). Differential input voltage  $V_{ID}$  is defined as ABS(IN+-IN-). Output offset voltage  $V_{OS}$  is defined as the average of the LVDS single-ended output voltages at logic high and logic low states. (3)
- Not production tested. Guaranteed by a statistical analysis on a sample basis at the time of characterization. (4)

<sup>(2)</sup> 

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RUMENTS

#### **Electrical Characteristics (continued)**

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	<b>Typ</b> (1)	Max	Units
t <sub>JIT</sub>	Jitter (0% Pre-emphasis)	RJ - Alternating 1 and 0 at 750 MHz <sup>(6)</sup>		0.5	1.5	ps
	(5)	DJ - K28.5 Pattern, 1.5 Gbps <sup>(7)</sup>		14	30	ps
		TJ - PRBS 2 <sup>23</sup> -1 Pattern, 1.5 Gbps <sup>(8)</sup>		14	31	ps
t <sub>ON</sub>	LVDS Output Enable Time	Time from $\overline{\text{PWDN}}$ to $\text{OUT} \pm \text{change from TRI-STATE to active.}$ Figure 9, Figure 10			20	μs
t <sub>OFF</sub>	LVDS Output Disable Time	Time from $\overline{\text{PWDN}}$ to $\text{OUT}\pm$ change from active to TRI-STATE. Figure 9, Figure 10			12	ns

(5) Jitter is not production tested, but guaranteed through characterization on a sample basis.

(6) Random Jitter, or RJ, is measured RMS with a histogram including 1500 histogram window hits. Stimulus and fixture Jitter has been subtracted. The input voltage = V<sub>ID</sub> = 500 mV, input common mode voltage = V<sub>ICM</sub> = 1.2V, 50% duty cycle at 750 MHz, t<sub>r</sub> = t<sub>f</sub> = 50 ps (20% to 80%).

(7) Deterministic Jitter, or DJ, is a peak to peak value. Stimulus and fixture jitter has been subtracted. The input voltage = V<sub>ID</sub> = 500 mV, input common mode voltage = V<sub>ICM</sub> = 1.2V, K28.5 pattern at 1.5 Gbps, t<sub>r</sub> = t<sub>f</sub> = 50 ps (20% to 80%). The K28.5 pattern is repeating bit streams of (0011111010 1100000101).

(8) Total Jitter, or TJ, is measured peak to peak with a histogram including 3500 window hits. Stimulus and fixture Jitter has been subtracted. The input voltage = V<sub>ID</sub> = 500 mV, input common mode voltage = V<sub>ICM</sub> = 1.2V, 2<sup>23</sup>-1 PRBS pattern at 1.5 Gbps, t<sub>r</sub> = t<sub>f</sub> = 50 ps (20% to 80%).

## **DC Test Circuits**

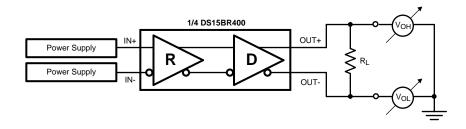


Figure 5. Differential Driver DC Test Circuit

### **AC Test Circuits and Timing Diagrams**

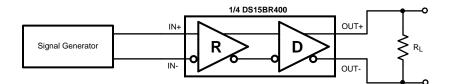


Figure 6. Differential Driver AC Test Circuit

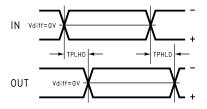


Figure 7. Propagation Delay Timing Diagram



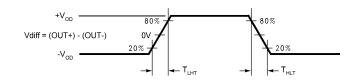


Figure 8. LVDS Output Transition Times

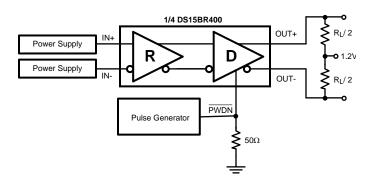


Figure 9. Enable/Disable Time Test Circuit

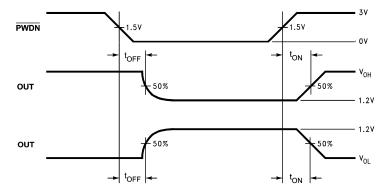


Figure 10. Enable/Disable Time Diagram

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## APPLICATION INFORMATION

#### **INTERNAL TERMINATIONS**

The DS15BR400 has integrated termination resistors on both the input and outputs. The inputs have a  $100\Omega$  resistor across the differential pair, placing the receiver termination as close as possible to the input stage of the device. The LVDS outputs also contain an integrated  $100\Omega$  ohm termination resistor, this resistor is used to minimize the output return loss and does not take the place of the 100 ohm termination at the inputs to the receiving device. The integrated terminations improve signal integrity and decrease the external component count resulting in space savings. The DS15BR401 has  $100\Omega$  output terminations only.

## **OUTPUT CHARACTERISTICS**

The output characteristics of the DS15BRB400/DS15BR401 have been optimized for point-to-point backplane and cable applications, and are not intended for multipoint or multidrop signaling.

## POWERDOWN MODE

The PWDN input activates a hardware powerdown mode. When the powerdown mode is active (PWDN=L), all input and output buffers and internal bias circuitry are powered off. When exiting powerdown mode, there is a delay associated with turning on bandgap references and input/output buffer circuits as indicated in the LVDS Output Switching Characteristics

Upon asserting the power down function ( $\overline{PWDN} = Low$ ), and if the Pre-emphasis feature is enable, it is possible for the driver output to source current for a short amount of time lifting the output common mode to V<sub>DD</sub>. To prevent this occurrence, a load discharge pull down path can be used on either output (1 k $\Omega$  to ground recommended). Alternately, a commonly deployed external failsafe network will also provide this path (see INPUT FAILSAFE BIASING). The occurrence of this is application dependant, and parameters that will effect if this is of concern include: AC coupling, use of the powerdown feature, presence of the discharge path, presence of the failsafe biasing, the usage of the pre-emphasis feature, and input characteristics of the downstream LVDS Receiver.

### **PRE-EMPHASIS**

Pre-emphasis dramatically reduces ISI jitter from long or lossy transmission media. One pin is used to select the pre-emphasis level for all outputs, off or on. The pre-emphasis boost is approximately 6 dB at 750 MHz.

PEM	Pre-Emphasis
0	Off
1	On

#### Table 1. Pre-emphasis Control Selection Table

#### **INPUT FAILSAFE BIASING**

Failsafe biasing of the LVDS link should be considered if the downstream Receiver is ON and enabled when the source is in TRI-STATE, powered off, or removed. This will set a valid known input state to the active receiver. This is accomplished by using a pull up resistor to  $V_{DD}$  on the 'plus' line, and a pull down resistor to GND on the 'minus' line. Resistor values are in the 750 Ohm to several k $\Omega$  range. The exact value depends upon the desired common mode bias point, termination resistor(s) and desired input differential voltage setting. Please refer to application note AN-1194 "Failsafe Biasing of LVDS interfaces" for more information and a general discussion.

### DECOUPLING

Each power or ground lead of the DS15BR400 should be connected to the PCB through a low inductance path. For best results, one or more vias are used to connect a power or ground pin to the nearby plane. Ideally, via placement is immediately adjacent to the pin to avoid adding trace inductance. Placing power plane closer to the top of the board reduces effective via length and its associated inductance.



Bypass capacitors should be placed close to VDD pins. Small physical size capacitors, such as 0402, X7R, surface mount capacitors should be used to minimize body inductance of capacitors. Each bypass capacitor is connected to the power and ground plane through vias tangent to the pads of the capacitor. An X7R surface mount capacitor of size 0402 has about 0.5 nH of body inductance. At frequencies above 30 MHz or so, X7R capacitors behave as low impedance inductors. To extend the operating frequency range to a few hundred MHz, an array of different capacitor values like 100 pF, 1 nF, 0.03  $\mu$ F, and 0.1  $\mu$ F are commonly used in parallel. The most effective bypass capacitor can be built using sandwiched layers of power and ground at a separation of 2–3 mils. With a 2 mil FR4 dielectric, there is approximately 500 pF per square inch of PCB.

The center dap of the WQFN package housing the DS15BR400 should be connected to a ground plane through an array of vias. The via array reduces the effective inductance to ground and enhances the thermal performance of the WQFN package.

#### **INPUT INTERFACING**

The DS15BR400 and DS15BR401 accept differential signals and allow simple AC or DC coupling. With a wide common mode range, the DS15BR400 and DS15BR401 can be DC-coupled with all common differential drivers (i.e. LVPECL, LVDS, CML). The following three figures illustrate typical DC-coupled interface to common differential drivers. Note that the DS15BR400 inputs are internally terminated with a 100 $\Omega$  resistor while the DS15BR401 inputs are not, therefore the latter requires external input termination.

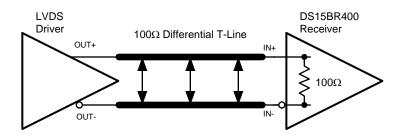


Figure 11. Typical LVDS Driver DC-Coupled Interface to DS15BR400 Input

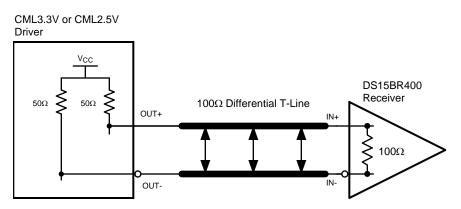


Figure 12. Typical CML Driver DC-Coupled Interface to DS15BR400 Input

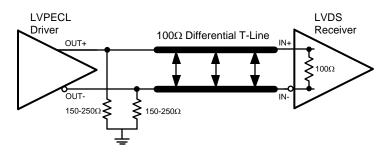


Figure 13. Typical LVPECL Driver DC-Coupled Interface to DS15BR400 Input



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### OUTPUT INTERFACING

The DS15BR400 and DS15BR401 output signals that are compliant to the LVDS standard. Their outputs can be DC-coupled to most common differential receivers. Figure 14 illustrates typical DC-coupled interface to common differential receivers and assumes that the receivers have high impedance inputs. While most differential receivers have a common mode input range that can accomodate LVDS compliant signals, it is recommended to check respective receiver's data sheet prior to implementing the suggested interface implementation.

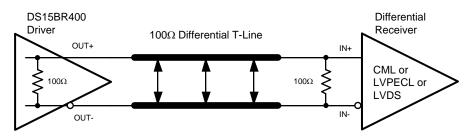


Figure 14. Typical DS15BR400 Output DC-Coupled Interface to an LVDS, CML or LVPECL Receiver

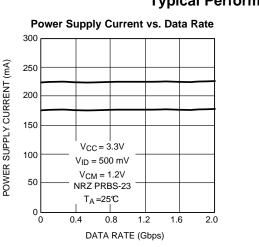
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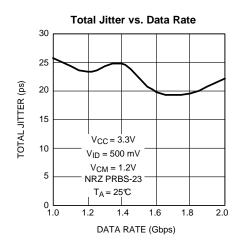
XAS

**ISTRUMENTS** 

Typical Performance Characteristics



#### Figure 15.





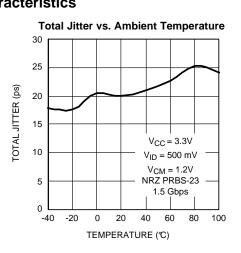


Figure 16.



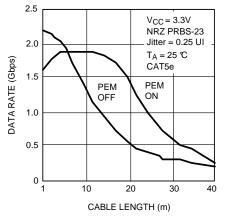
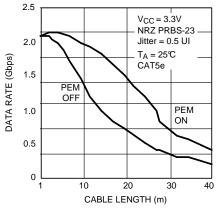


Figure 18. (1)







(1) Data presented in this graph was collected using the DS15BR400EVK, a pair of RJ-45 to SMA adapter boards and various length Belden 1700a cables. The maximum data rate was determined based on total jitter (0.25 UI criteria) measured after the cable. The total jitter was a peak to peak value measured with a histogram including 3000 window hits.



9-Mar-2013

# **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
DS15BR400TSQ	ACTIVE	WQFN	RTV	32	1000	TBD	Call TI	Call TI	-40 to 85	5R400SQ	Samples
DS15BR400TSQ/NOPB	ACTIVE	WQFN	RTV	32	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	5R400SQ	Samples
DS15BR400TSQX/NOPB	ACTIVE	WQFN	RTV	32	4500	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	5R400SQ	Samples
DS15BR400TVS	ACTIVE	TQFP	PFB	48	250	TBD	Call TI	Call TI	-40 to 85	DS15BR 400TVS	Samples
DS15BR400TVS/NOPB	ACTIVE	TQFP	PFB	48	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	DS15BR 400TVS	Samples
DS15BR400TVSX	ACTIVE	TQFP	PFB	48	1000	TBD	Call TI	Call TI	-40 to 85	DS15BR 400TVS	Samples
DS15BR400TVSX/NOPB	ACTIVE	TQFP	PFB	48	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	DS15BR 400TVS	Samples
DS15BR401TSQ	ACTIVE	WQFN	RTV	32	1000	TBD	Call TI	Call TI	-40 to 85		Samples
DS15BR401TSQ/NOPB	ACTIVE	WQFN	RTV	32	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	5R401SQ	Samples
DS15BR401TSQX	ACTIVE	WQFN	RTV	32	4500	TBD	Call TI	Call TI	-40 to 85		Samples
DS15BR401TSQX/NOPB	ACTIVE	WQFN	RTV	32	4500	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	5R401SQ	Samples
DS15BR401TVS	ACTIVE	TQFP	PFB	48	250	TBD	Call TI	Call TI	-40 to 85	DS15BR 401TVS	Samples
DS15BR401TVS/NOPB	ACTIVE	TQFP	PFB	48	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	DS15BR 401TVS	Samples
DS15BR401TVSX	ACTIVE	TQFP	PFB	48	1000	TBD	Call TI	Call TI	-40 to 85	DS15BR 401TVS	Samples
DS15BR401TVSX/NOPB	ACTIVE	TQFP	PFB	48	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	DS15BR 401TVS	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.



9-Mar-2013

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> Only one of markings shown within the brackets will appear on the physical device.

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## TAPE AND REEL INFORMATION





# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



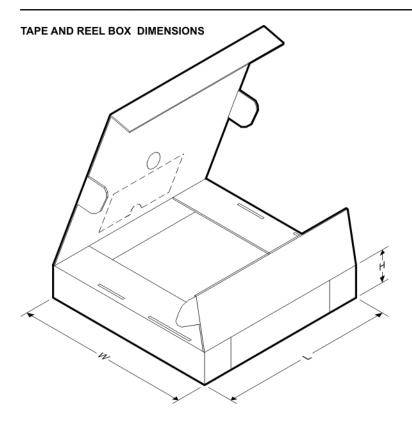
All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS15BR400TSQ	WQFN	RTV	32	1000	178.0	12.4	5.3	5.3	1.3	8.0	12.0	Q1
DS15BR400TSQ/NOPB	WQFN	RTV	32	1000	178.0	12.4	5.3	5.3	1.3	8.0	12.0	Q1
DS15BR400TSQX/NOPB	WQFN	RTV	32	4500	330.0	12.4	5.3	5.3	1.3	8.0	12.0	Q1
DS15BR400TVSX	TQFP	PFB	48	1000	330.0	16.4	9.3	9.3	2.2	12.0	16.0	Q2
DS15BR400TVSX/NOPB	TQFP	PFB	48	1000	330.0	16.4	9.3	9.3	2.2	12.0	16.0	Q2
DS15BR401TSQ/NOPB	WQFN	RTV	32	1000	178.0	12.4	5.3	5.3	1.3	8.0	12.0	Q1
DS15BR401TSQX/NOPB	WQFN	RTV	32	4500	330.0	12.4	5.3	5.3	1.3	8.0	12.0	Q1
DS15BR401TVSX	TQFP	PFB	48	1000	330.0	16.4	9.3	9.3	2.2	12.0	16.0	Q2
DS15BR401TVSX/NOPB	TQFP	PFB	48	1000	330.0	16.4	9.3	9.3	2.2	12.0	16.0	Q2

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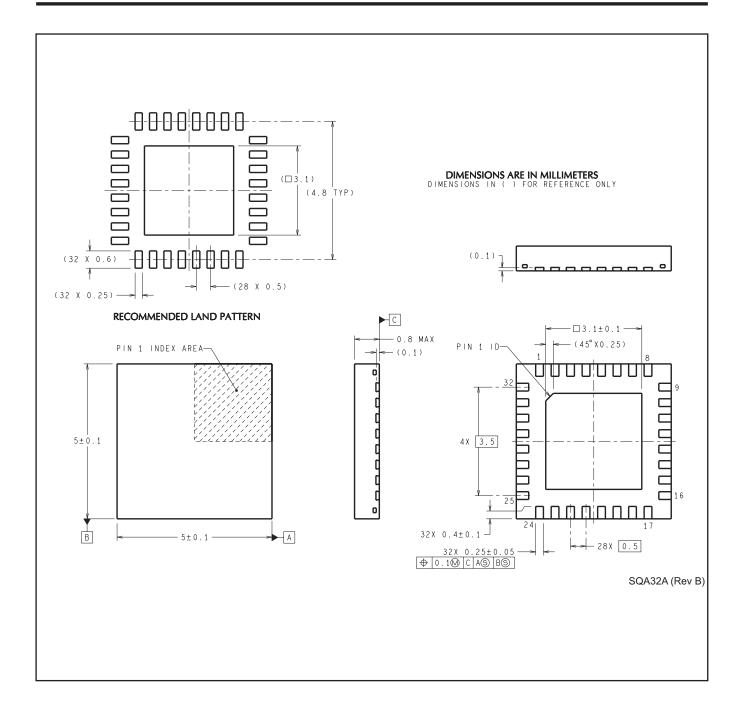
26-Mar-2013



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS15BR400TSQ	WQFN	RTV	32	1000	213.0	191.0	55.0
DS15BR400TSQ/NOPB	WQFN	RTV	32	1000	213.0	191.0	55.0
DS15BR400TSQX/NOPB	WQFN	RTV	32	4500	367.0	367.0	35.0
DS15BR400TVSX	TQFP	PFB	48	1000	367.0	367.0	38.0
DS15BR400TVSX/NOPB	TQFP	PFB	48	1000	367.0	367.0	38.0
DS15BR401TSQ/NOPB	WQFN	RTV	32	1000	213.0	191.0	55.0
DS15BR401TSQX/NOPB	WQFN	RTV	32	4500	367.0	367.0	35.0
DS15BR401TVSX	TQFP	PFB	48	1000	367.0	367.0	38.0
DS15BR401TVSX/NOPB	TQFP	PFB	48	1000	367.0	367.0	38.0

# **MECHANICAL DATA**

# RTV0032A





# **MECHANICAL DATA**

MTQF019A - JANUARY 1995 - REVISED JANUARY 1998

#### PFB (S-PQFP-G48)

PLASTIC QUAD FLATPACK



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-026



PFB (S-PQFP-G48)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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